

Approved <i>M. Yamaguchi</i>	Checked <i>T. Shinda</i>	Designed <i>K. Takahashi</i>	DEVELOPMENT SPECIFICATION				17	4
			P/N LNJ308G8PRA					
T Y P E	Green Light Emitting Diode							
APPLICATION	Indicators							
MATERIAL	GaP							
OUTLINE	Attached							
ABSOLUTE MAXIMUM RATINGS	P 50 mW	※IFP 100 mA	IFDC 20 mA	VR 4 V	Topr -25~+85 ℃	Tstg -40~+100 ℃		
CONDITION	Ta=25±3 ℃							

Test Specification

Item	Symbol	Condition	Typ	Limit		Unit
				Min	Max	
Forward Voltage	V _F	IF= 10 mA	2.03		2.6	V
Reverse Leakage Current	I _R	VR= 4 V			10	μA
Luminous Intensity	I _o	IF= 10 mA·DC	0.7	0.25		mcđ
Peak Emission Wavelength	λ _P	IF= 10 mA·DC	555			nm
Spectral Line Half Width	Δλ	IF= 10 mA·DC	20			nm

※ The Condition of IFP is duty 10 % , Pulse width 1 ms
 · Please contact the Panasonic local office if you design
 at low current (below 1 mA DC) or pulse current operation
 and have any questions.

NOTE

- ★1 Terminal:Plated with gold on copper base.
- ★2 Package:Light green diffusion type.
- ★3 Soldering conditions.
Refer to Handling note.
- ★4 Care should be taken that soldering is done within 3-days after
opening the drypackage and reel.

Aug. 26. 1998		

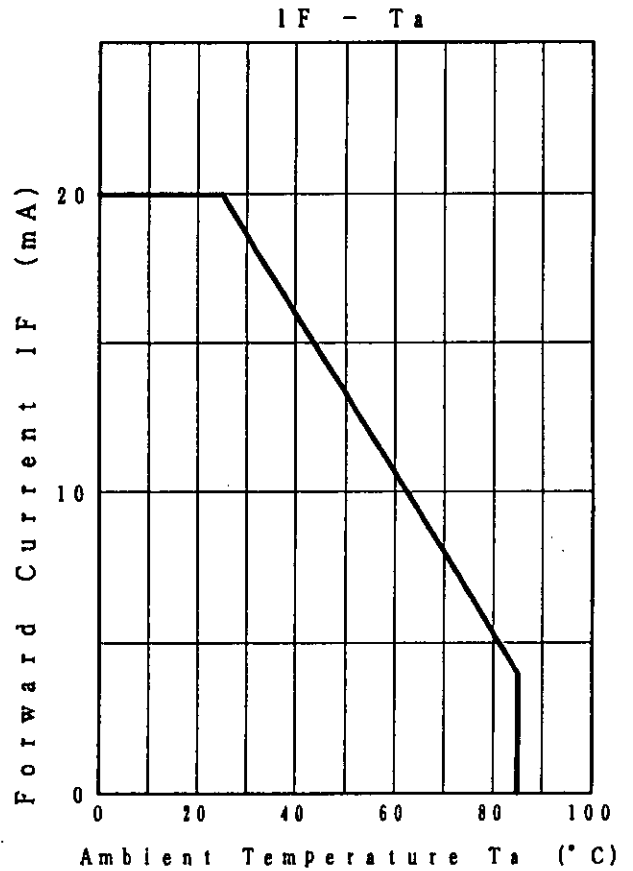
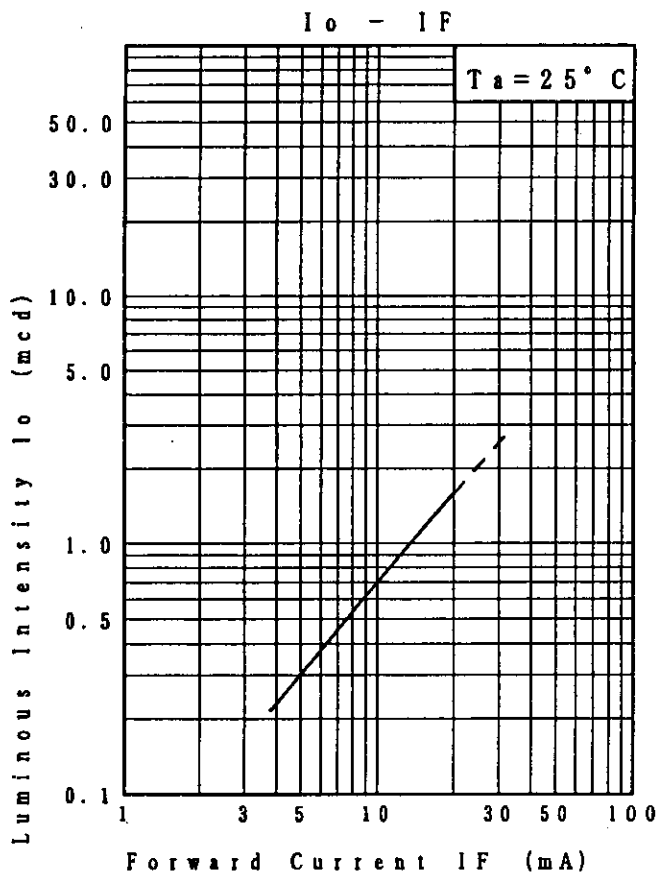
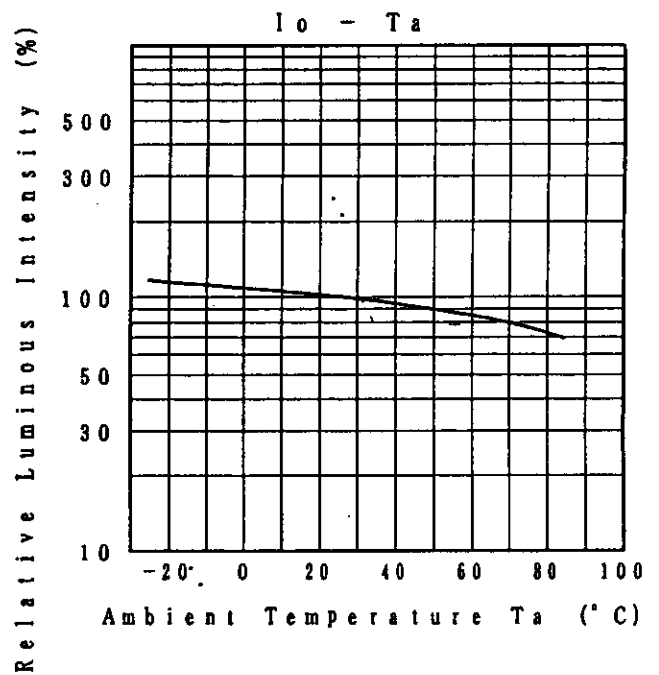
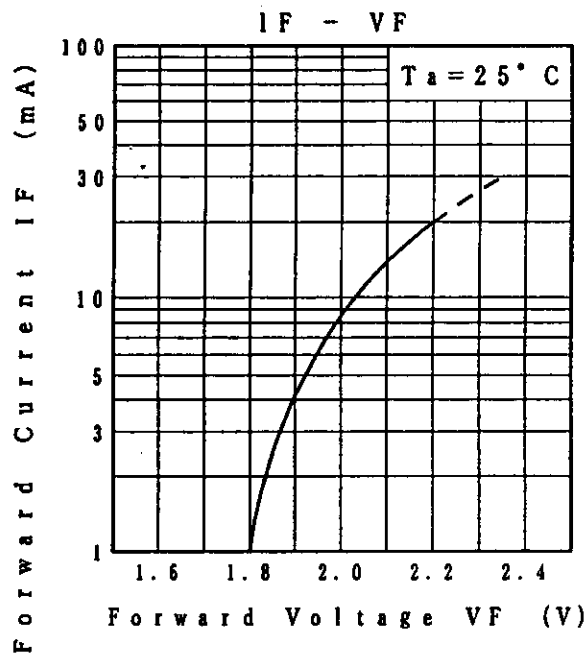
Approved <i>M. Yamaguchi</i>	Checked <i>T. Okada</i>	Designed <i>K. Shibata</i>
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DEVELOPMENT SPECIFICATION

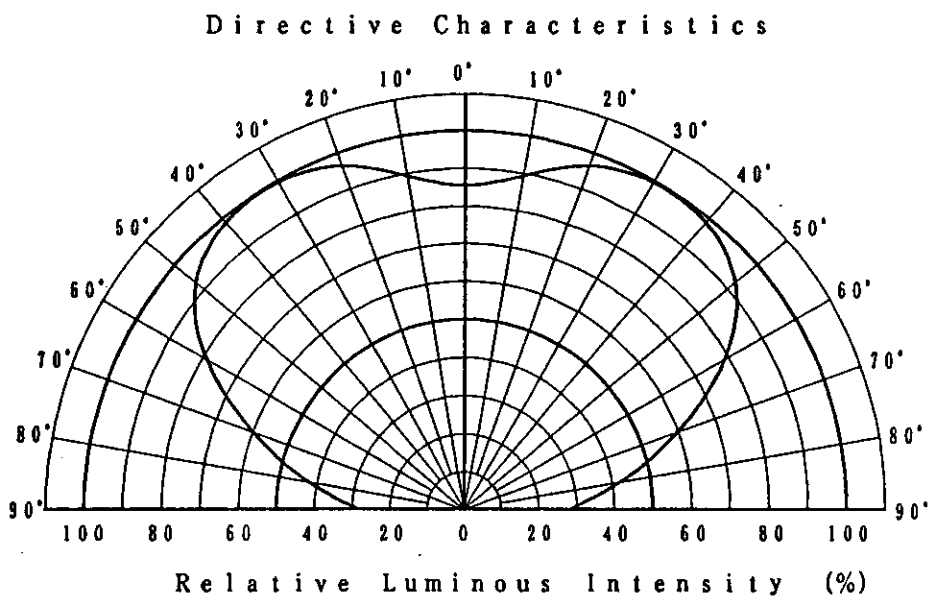
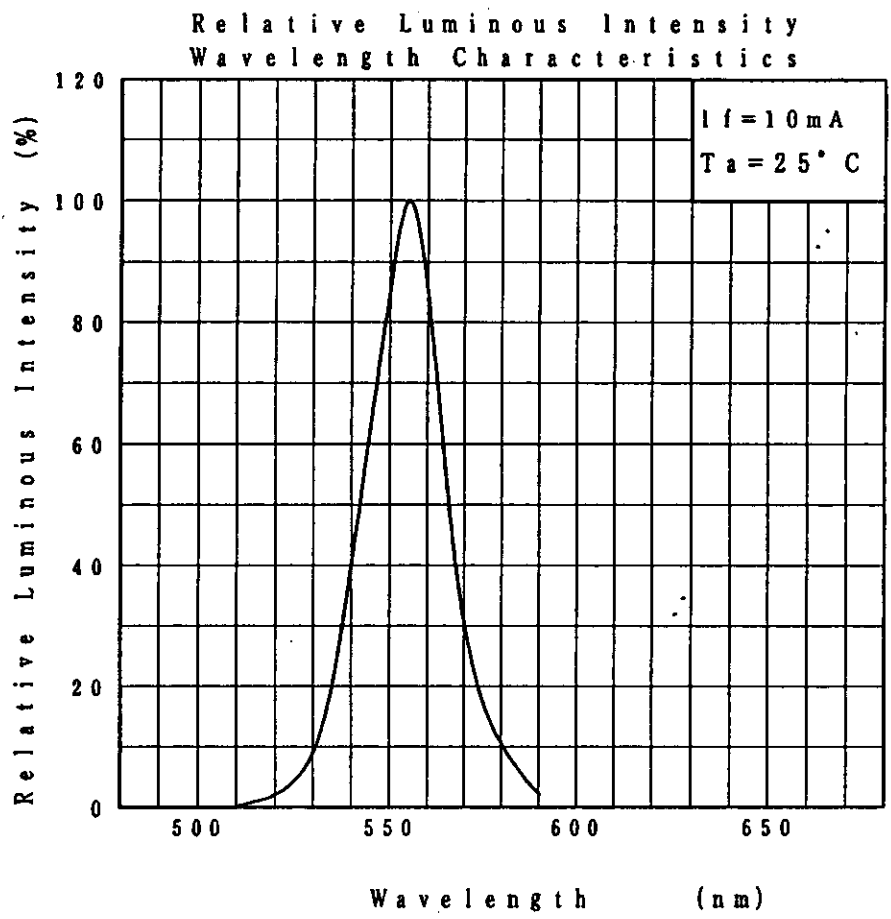
P/N: LNJ308G8PRA

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Aug. 26. 1998



Aug. 26. 1998		
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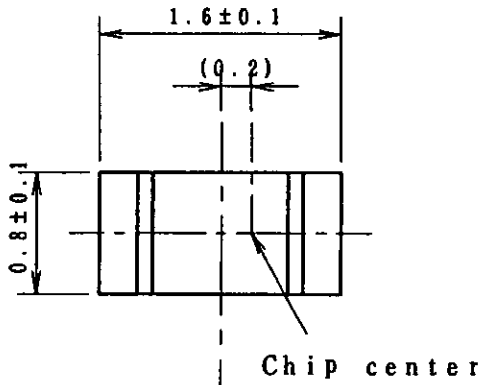
A. Yamaguchi | *T. Akeda* | *K. Sakurai*

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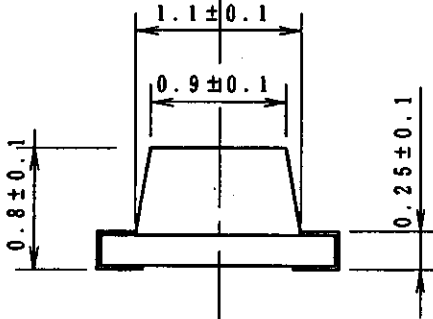
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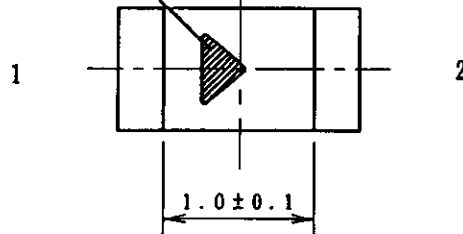
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Chip center



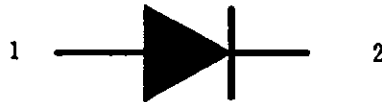
Polarity mark



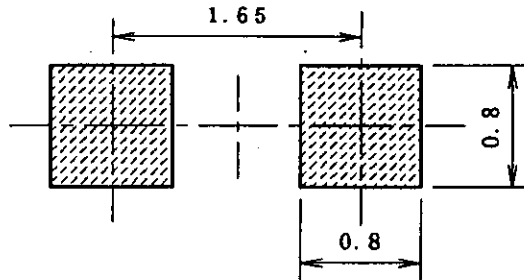
Polarity

1: Anode

2: Cathode



Recommended land layout



(NOTE)

1. Measurement of the package doesn't include electrode projection.
2. Unit: mm

Aug. 26. 1998